2014年第27期(总第332期）

凝聚态物理–北京大学论坛

IC

Abstract Reduction of Standby current for all electronic application is the desire While feature size keeps shrinking from 90nm to 65, 40, 28, 14nm, the increasing of device leakage become the major show stopper. This seminar will Introduce a novel methodology to resolve the above problem and achieved improvement wafer yield by 50%.

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时间：12月18日（星期四）15:00—16:40

地点：北京大学物理大楼中212教室

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Photograph by Xiaodong Hu